

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of:

Varun Singh, et al.

Serial No.: Not Assigned

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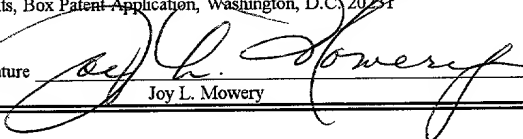
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Previous Examiner: H. Tsai

Previous Group Art Unit: 2812

For: AN IMPROVED POLYSILICON RESISTOR HAVING ADJUSTABLE  
TEMPERATURE COEFFICIENTS AND THE METHOD OF MAKING THE  
SAME

BOX: Patent Application  
Assistant Commissioner For Patents  
Washington, D.C. 20231

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Dear Sir:

**PRELIMINARY AMENDMENT**

Prior to the examination of the above-identified application, please amend this application as follows:

**IN THE CLAIMS**

Please cancel Claims 3-10 and 13-15. Claims 1-2 and 11-12 remain for consideration in this application.

1. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of from  $\sim 6 \times 10^{19} \text{ cm}^{-3}$  to  $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$ .

2. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of less than  $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$ .

11. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of greater than  $\sim 6 \times 10^{19} \text{ cm}^{-3}$ .

12. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a late implant doping technique.

**REMARKS**

In view of the above, it is believed that this application is in condition for allowance, and such a Notice is respectfully requested.

Respectfully submitted,

JENKENS & GILCHRIST  
A Professional Corporation



Stuart D. Dwork  
Reg. No. 31,103

1445 Ross Avenue, Suite 3200  
Dallas, Texas 75202-2799  
214/855-4727  
214/855-4300 (fax)

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